$$d \ll H_c$$

$$C_{top} = \frac{F_{x,in} / A_{in}}{V_{in} + \frac{e^{-\left(\frac{H_c}{d}\right)^2 / A_{in}}}{erf\left(H_c/d\right) \sqrt{\frac{2D_{ab}v_{in}}{\pi H_c}}}$$

$$C_{top} = \frac{F_{x,in}}{A_{in} v_{in}} \equiv C_{in}$$
 input concentration if diffusion doesn't occur

after some algebra...

$$J_{dep} = D_{ab} \frac{dC}{dz} \bigg|_{bottom} = D_{ab} \frac{C_{in}}{\underbrace{erf(H_c/d)}_{\approx 1}} \frac{2}{d\sqrt{\pi}}$$

$$J_{dep} = F_{x,in} \sqrt{\frac{2D_{ab}}{\pi v_{in} H_c}}$$

$$\eta = \sqrt{\frac{2D_{ab}}{\pi v_{in} H_c}}$$

As we go faster there's less time for species to diffuse to the wafer; efficiency falls as the square root of the input velocity, even though deposition rate is increased vs. the pure-diffusion case.